Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H1068

APPLICATIONS

audio amplifier.

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……750mW

V_{CBO}——Collector-Base Voltage……-20V

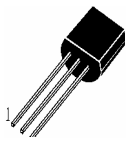
V_{CEO}——Collector-Emitter Voltage……-16V

V_{EBO}——Emitter-Base Voltage……-6V

I_C——Collector Current（DC）…… -2A

I_{CP}——Collector Current（Pulse）……-3A

TO-92



1—Emitter，E
2—Collector，C
3—Base，B

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-20			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-16			V	I_C=-10mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	-6			V	I_E=-1mA，I_C=0
H_{FE}（1）	DC Current Gain	135	350	650		V_{CE}=-2V, I_C=-100mA
H_{FE}（2）	DC Current Gain	100				V_{CE}=-2V, I_C=-1.5A
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage		-0.25	-0.4	V	I_C=-1A, I_B=-10mA
$V_{CE(sat2)}$	Collector- Emitter Saturation Voltage		-0.31	-0.5	V	I_C=-1.5A, I_B=-75mA
$V_{CE(sat3)}$	Collector- Emitter Saturation Voltage		-0.33	-0.5	V	I_C=-1.5A, I_B=-20mA
V_{BE}	Base-Emitter Voltage	-550	-600	-650	mV	V_{CE}=-6V, I_C=-5.0mA
I_{CBO}	Collector Cut-off Current			-100	nA	V_{CB}=-16V, I_E=0
I_{EBO}	Emitter Cut-off Current			-100	nA	V_{EB}=-6V, I_C=0
f_T	Current Gain-Bandwidth Product	100	180		MHz	V_{CE}=-10V, I_C=-50mA
Cob	Output Capacitance		60		pF	V_{CB}=-10V, I_E=0，f=1MHz

h_{FE} Classification

L	K	U
135—270	200—400	300—650